



#### **DUAL P-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

V <sub>(BR)DSS</sub>	RDS(ON) max	I <sub>D MAX</sub> T <sub>A</sub> = +25°C
-20V	$70m\Omega$ @ $V_{GS} = -4.5V$	-3.8A
-20 V	$85m\Omega$ @ $V_{GS} = -2.5V$	-3.3A

### **Description**

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

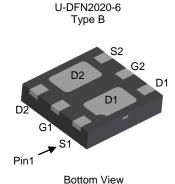
- Load Switch
- Power Management Functions
- Portable Power Adaptors

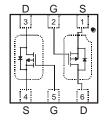
#### **Features**

- Low On-Resistance
- Low Gate Threshold Voltage, -0.9V Max
- Fast Switching Speed
- Low Input/Output Leakage
- Low Profile, 0.5mm Max Height
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

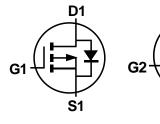
### **Mechanical Data**

- Case: U-DFN2020-6 Type B
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu Annealed over Copper Leadframe.
  Solderable per MIL-STD-202, Method 208
- Weight: 0.0065 grams (Approximate)





Top View Internal Schematic



Q1 P-CHANNEL

Q2 P-CHANNEL

S<sub>2</sub>

**D2** 

Internal Schematic

## Ordering Information (Note 5)

Part Number	Case	Packaging
DMP2160UFDBQ-7	U-DFN2020-6 Type B	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_grade\_definitions/
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



## **Marking Information**



P2 = Marking Code YM = Date Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September) Dot denotes Pin 1

Date Code Key

Year	2008	2009	2010	2011	201	2 20	13	2014	2015	2016	2017	2018
Code	V	W	Х	Y	Z		4	В	С	D	Е	F
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

### Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	$V_{DSS}$	-20	V
Gate-Source Voltage	$V_{GSS}$	±12	V
Drain Current (Note 6)	I <sub>D</sub>	-3.8	А
Pulsed Drain Current (Note 7)	I <sub>DM</sub>	-13	Α

# Thermal Characteristics (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	$P_{D}$	1.4	W
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	89	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

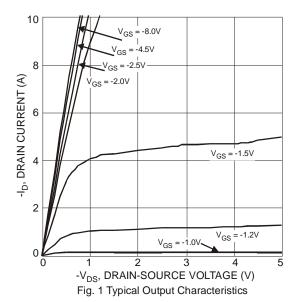
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

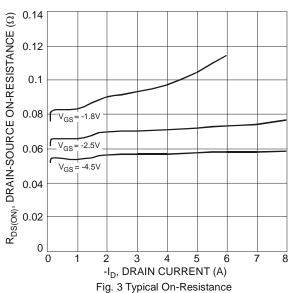
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)	Syllibol	IVIIII	Тур	IVIAX	Ollit	rest condition
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1	μΑ	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100 ±800	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$ $V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)	•	•				
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.45		-0.9	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
		_	54	70		$V_{GS} = -4.5V$ , $I_D = -2.8A$
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)	_	68	85	$m\Omega$	$V_{GS} = -2.5V$ , $I_D = -2.0A$
		_	86	_		$V_{GS} = -1.8V, I_D = -1.0A$
Forward Transfer Admittance	Y <sub>fs</sub>	_	8	_	S	$V_{DS} = -5V, I_D = -2.8A$
Diode Forward Voltage (Note 8)	V <sub>SD</sub>		0.7	-1.2	٧	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1.6A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C <sub>iss</sub>	_	536	—	pF	101/1/
Output Capacitance	Coss	_	68	_	pF	$V_{DS} = -10V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	59	_	рF	1 = 1.01/11 12
Gate Resistance	$R_g$		8.72		Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$
Total Gate Charge	Qg		6.5		nC	V <sub>GS</sub> = -4.5V, V <sub>DD</sub> = -10V,
Gate-Source Charge	Q <sub>gs</sub>	_	0.8	_	nC	VGS = -4.5V, VDD = -10V, ID = -1.5A
Gate-Drain Charge	Q <sub>qd</sub>	_	1.4	_	nC	10 - 1.07
Turn-On Delay Time	t <sub>D(on)</sub>		11.51	_	ns	
Turn-On Rise Time	tr	_	12.09	_	ns	$V_{GEN} = -4.5V, V_{DD} = -10V,$
Turn-Off Delay Time	t <sub>D(off)</sub>	_	55.34	_	ns	$R_L = 10\Omega$ , $R_G = 6\Omega$
Turn-Off Fall Time	t <sub>f</sub>	_	27.54	_	ns	

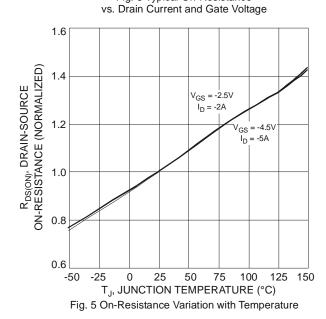
Notes:

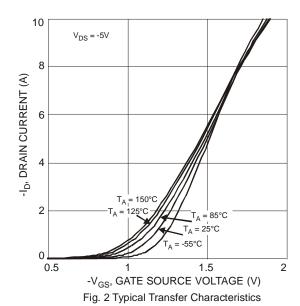
- 6. Device mounted on FR-4 PCB, on minimum recommended, 2oz Copper pad layout.
- 7. Repetitive rating, pulse width limited by junction temperature.
- 3. Short duration pulse test used to minimize self-heating effect.











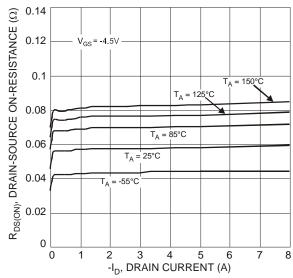


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

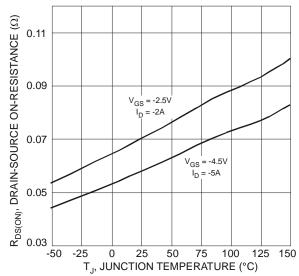
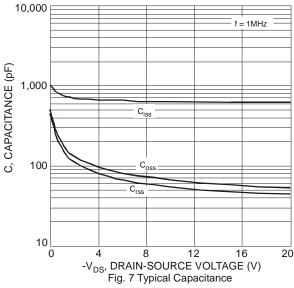
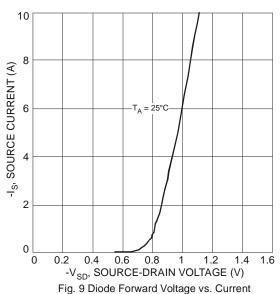


Fig. 6 On-Resistance Variation with Temperature







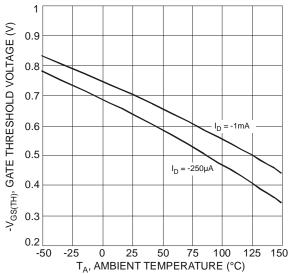


Fig. 8 Gate Threshold Variation vs. Ambient Temperature

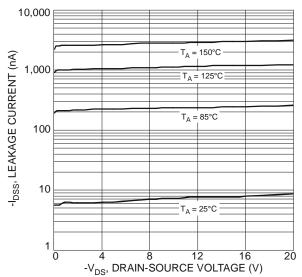


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

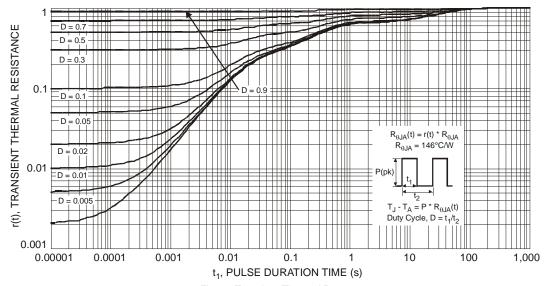
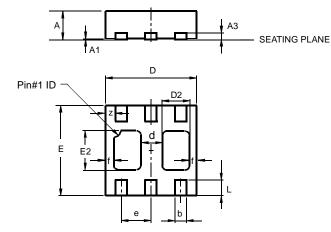


Fig. 11 Transient Thermal Response



## **Package Outline Dimensions**

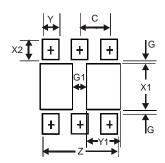
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



U-DFN2020-6 Type B							
Dim	Min	Min Max Typ					
Α	0.545	0.605	0.575				
A1	0	0.05	0.02				
A3		_	0.13				
b	0.20	0.30	0.25				
D	1.95	2.075	2.00				
d		_	0.45				
D2	0.50	0.70	0.60				
е	_	_	0.65				
Е	1.95	2.075	2.00				
E2	0.90	1.10	1.00				
f			0.15				
L	0.25	0.35	0.30				
z			0.225				
All Dimensions in mm							

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	1.67
G	0.20
G1	0.40
X1	1.0
X2	0.45
Y	0.37
Y1	0.70
С	0.65



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